# P-Channel 12 V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---|---|---|---|
| $V_{DS}$ (V) | $R_{DS(on)}$ (Ω) | $I_D$ (A) | $Q_g$ (Typ.) |
| - 12 | 0.130 at $V_{GS}$ = - 4.5 V | 1.18 | 6.7 |
| | 0.158 at $V_{GS}$ = - 2.5V | 1.07 | |
| | 0.205 at $V_{GS}$ = - 1.8V | 0.49 | |

## FEATURES

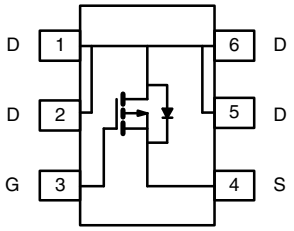
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % $R_g$ Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE

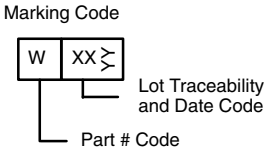
## APPLICATIONS

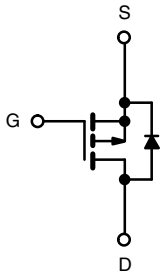
- Load Switch for Portable Devices

**SC-89 (6-LEADS)**




Top View




P-Channel MOSFET

**Ordering Information:** Si1065X-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25 °C, unless otherwise noted) | | | | |
|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Limit** | **Unit** |
| Drain-Source Voltage | | $V_{DS}$ | - 12 | V |
| Gate-Source Voltage | | $V_{GS}$ | ± 8 | |
| Continuous Drain Current ($T_J$ = 150 °C) | $T_A$ = 25 °C | $I_D$ | - 1.18[b, c] | A |
| | $T_A$ = 70 °C | | - 0.94[b, c] | |
| Pulsed Drain Current | | $I_{DM}$ | - 8 | |
| Continuous Source-Drain Diode Current | $T_A$ = 25 °C | $I_S$ | - 0.2[b, c] | |
| Maximum Power Dissipation[a] | $T_A$ = 25 °C | $P_D$ | 0.236[b, c] | W |
| | $T_A$ = 70 °C | | 0.151[b, c] | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Typical** | **Maximum** | **Unit** |
| Maximum Junction-to-Ambient[a, b] | t ≤ 5 s | $R_{thJA}$ | 440 | 530 | °C/W |
| | Steady State | | 540 | 650 | |

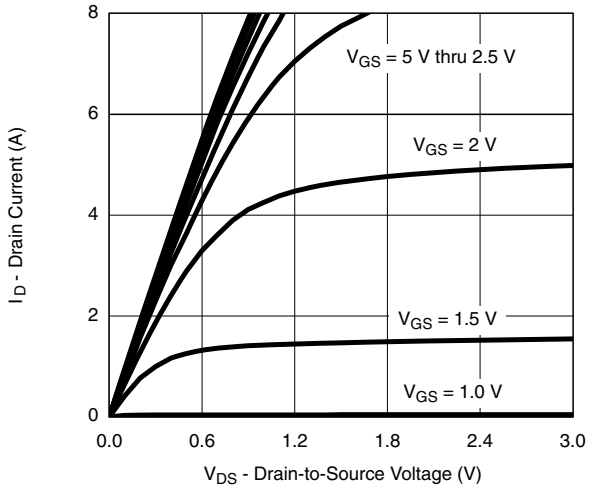
Notes:
a. Maximum under steady state conditions is 650 °C/W.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.

| **SPECIFICATIONS** ($T_J$ = 25 °C, unless otherwise noted) | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | **Min.** | **Typ.** | **Max.** | **Unit** |
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = - 250 µA | - 12 | | | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D$ = - 250 µA | | - 8.47 | | mV/°C |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | 2.33 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = - 250 µA | - 0.45 | | - 0.95 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 8 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = - 12 V, $V_{GS}$ = 0 V | | | - 1 | nA |
| | | $V_{DS}$ = - 12 V, $V_{GS}$ = 0 V, $T_J$ = 85 °C | | | - 10 | µA |
| On-State Drain Current[a] | $I_{D(on)}$ | $V_{DS}$ = ≥ 5 V, $V_{GS}$ = - 4.5 V | - 8 | | | A |
| Drain-Source On-State Resistance[a] | $R_{DS(on)}$ | $V_{GS}$ = - 4.5 V, $I_D$ = - 1.18 A | | 0.108 | 0.130 | Ω |
| | | $V_{GS}$ = - 2.5 V, $I_D$ = - 1.07 A | | 0.131 | 0.158 | |
| | | $V_{GS}$ = - 1.8 V, $I_D$ = - 0.49 A | | 0.158 | 0.204 | |
| Forward Transconductance | $g_{fs}$ | $V_{DS}$ = - 6 V, $I_D$ = - 1.18 A | | 5.18 | | S |
| **Dynamic[b]** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ = - 6 V, $V_{GS}$ = 0 V, f = 1 MHz | | 480 | | pF |
| Output Capacitance | $C_{oss}$ | | | 190 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 145 | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = - 6 V, $V_{GS}$ = - 5 V, $I_D$ = - 1.18 A | | 7.2 | 10.8 | nC |
| | | $V_{DS}$ = - 6 V, $V_{GS}$ = - 4.5 V, $I_D$ = - 1.18 | | 6.7 | 10.1 | |
| Gate-Source Charge | $Q_{gs}$ | | | 0.84 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 2.7 | | |
| Gate Resistance | $R_g$ | f = 1 MHz | | 10 | 15 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = - 6 V, $R_L$ = 6.32 Ω<br>$I_D$ ≅ - 0.95 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 Ω | | 13 | 19.5 | ns |
| Rise Time | $t_r$ | | | 27 | 40.5 | |
| Turn-Off DelayTime | $t_{d(off)}$ | | | 45 | 67.5 | |
| Fall Time | $t_f$ | | | 27 | 40.5 | |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Pulse Diode Forward Current[a] | $I_{SM}$ | | | | 8 | A |
| Body Diode Voltage | $V_{SD}$ | $I_S$ = - 0.63 A | | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $I_F$ = - 0.7 A, dI/dt = 100 A/µs | | 29.2 | 44 | nC |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | | 10.22 | 15.3 | ns |
| Reverse Recovery Fall Time | $t_a$ | | | 13.7 | | |
| Reverse Recovery Rise Time | $t_b$ | | | 15.5 | | |

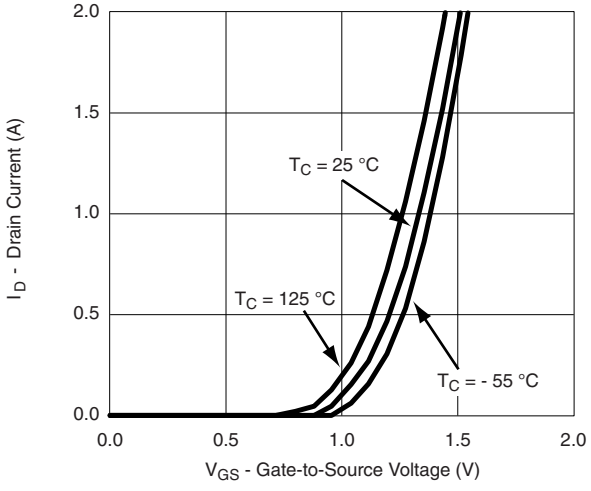
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

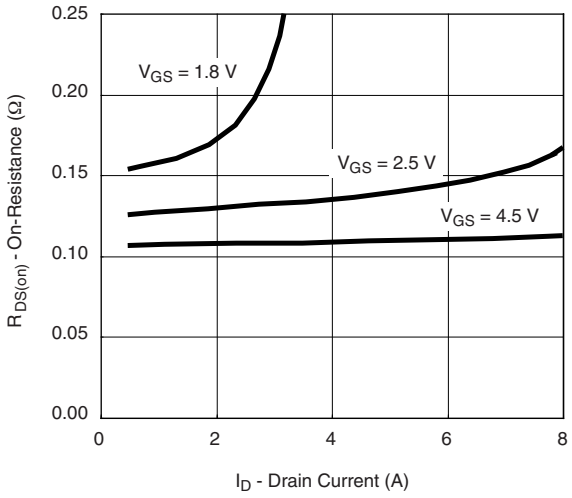
## TYPICAL CHARACTERISTICS ($T_A$ = 25 °C, unless otherwise noted)



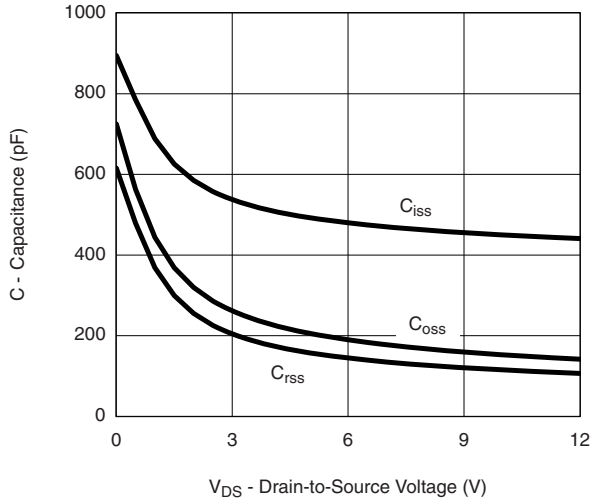

**Output Characteristics**



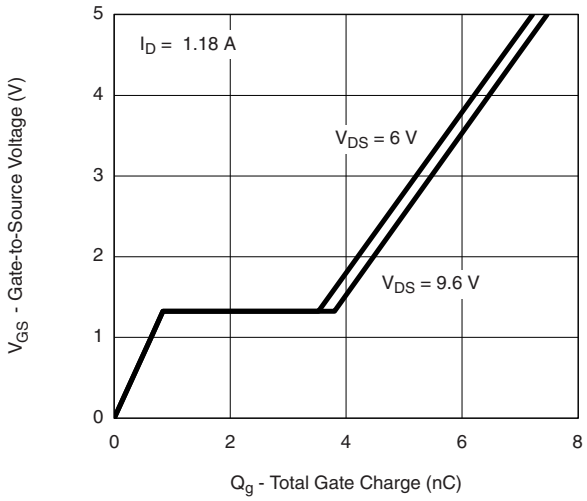

**Transfer Characteristics Curves vs. Temp.**



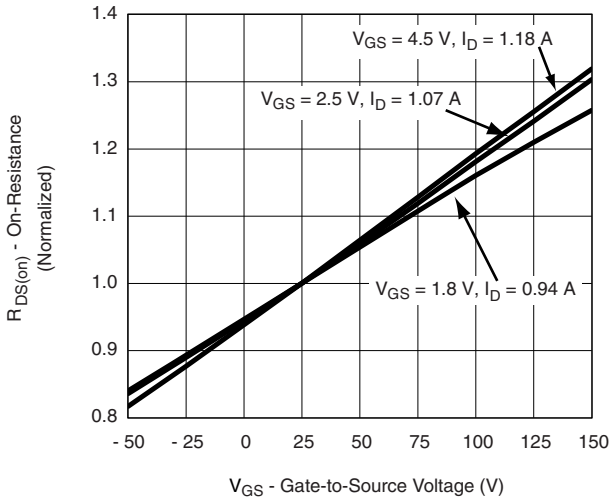

**On-Resistance vs. Drain Current**




**Capacitance**

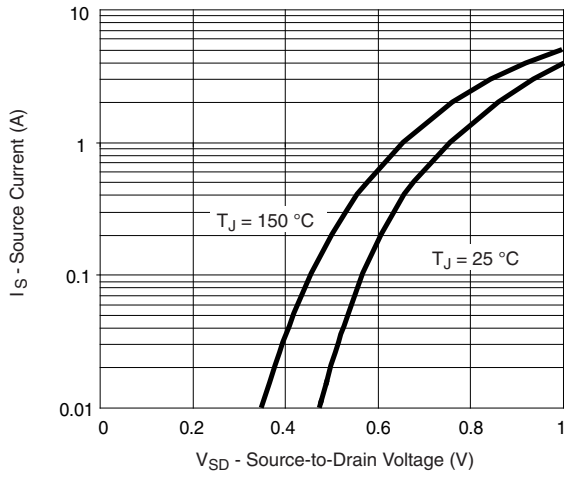



**Gate Charge**

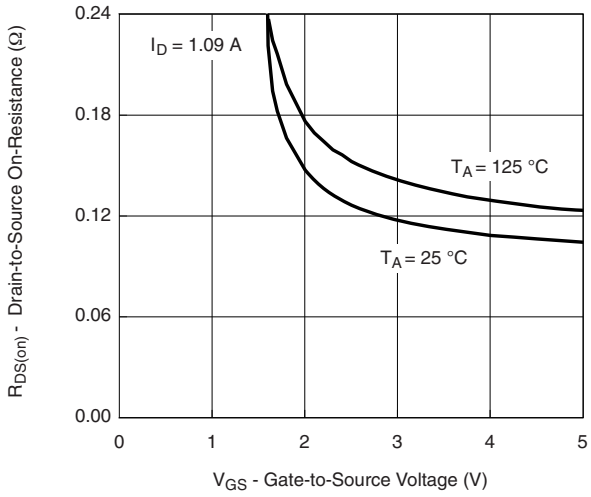



**On-Resistance vs. Junction Temperature**

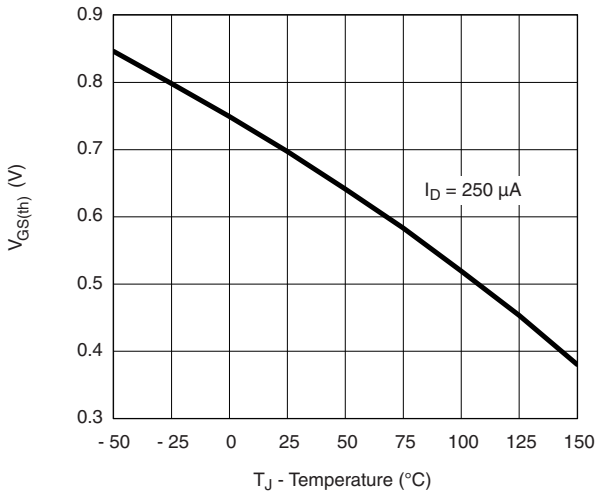
## TYPICAL CHARACTERISTICS ($T_A$ = 25 °C, unless otherwise noted)



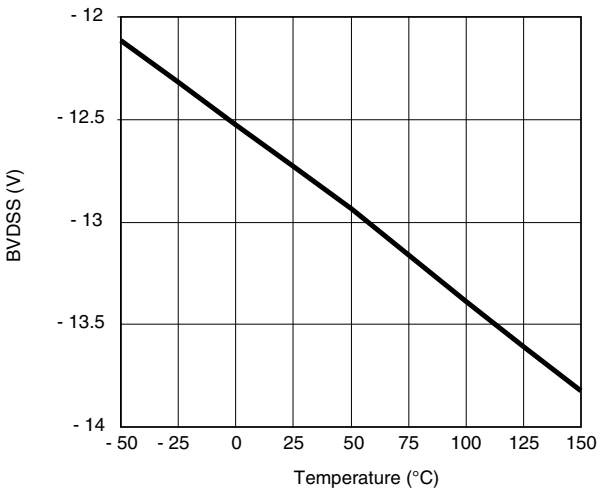

**Source-Drain Diode Forward Voltage**



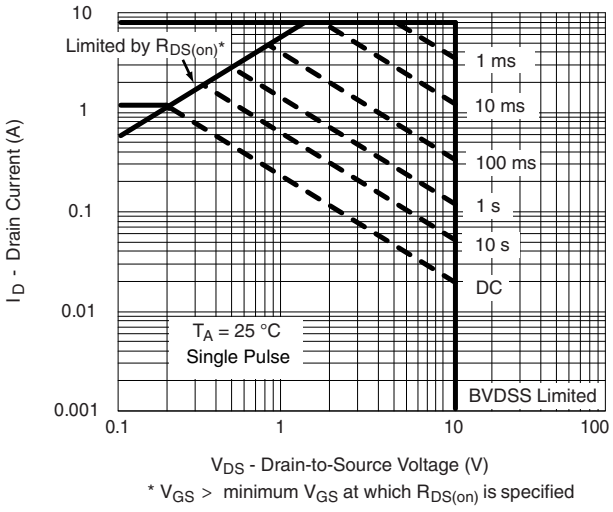

**$R_{DS(on)}$ vs. $V_{GS}$ vs. Temperature**




**Threshold Voltage**



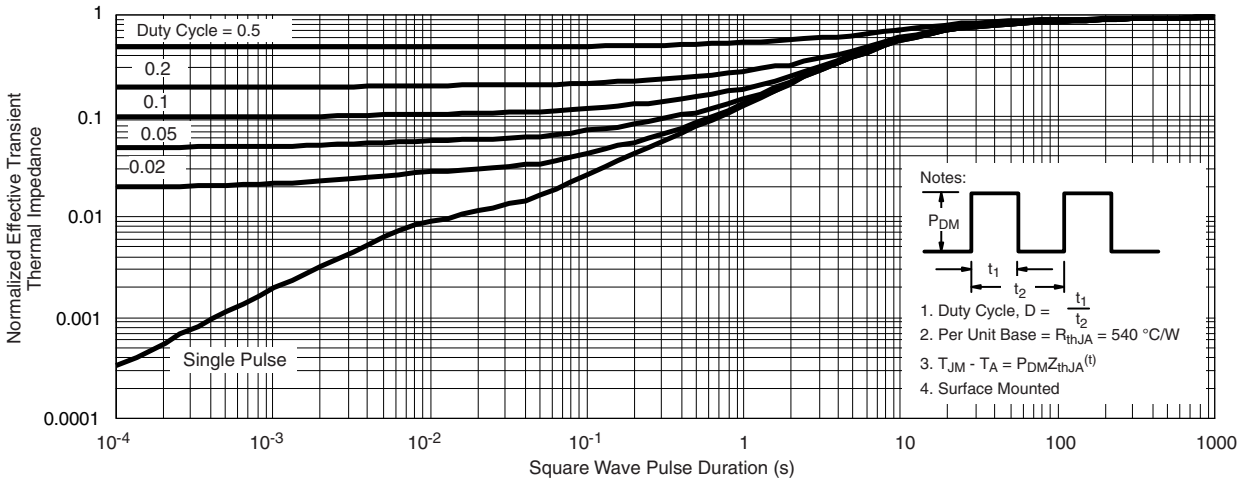

**BVDSS vs. Temparture**




* $V_{GS}$ > minimum $V_{GS}$ at which $R_{DS(on)}$ is specified

**Safe Operating Area, Junction-to-Ambient**

## TYPICAL CHARACTERISTICS ($T_A$ = 25 °C, unless otherwise noted)




**Normalized Thermal Transient Impedance, Junction-to-Ambient**

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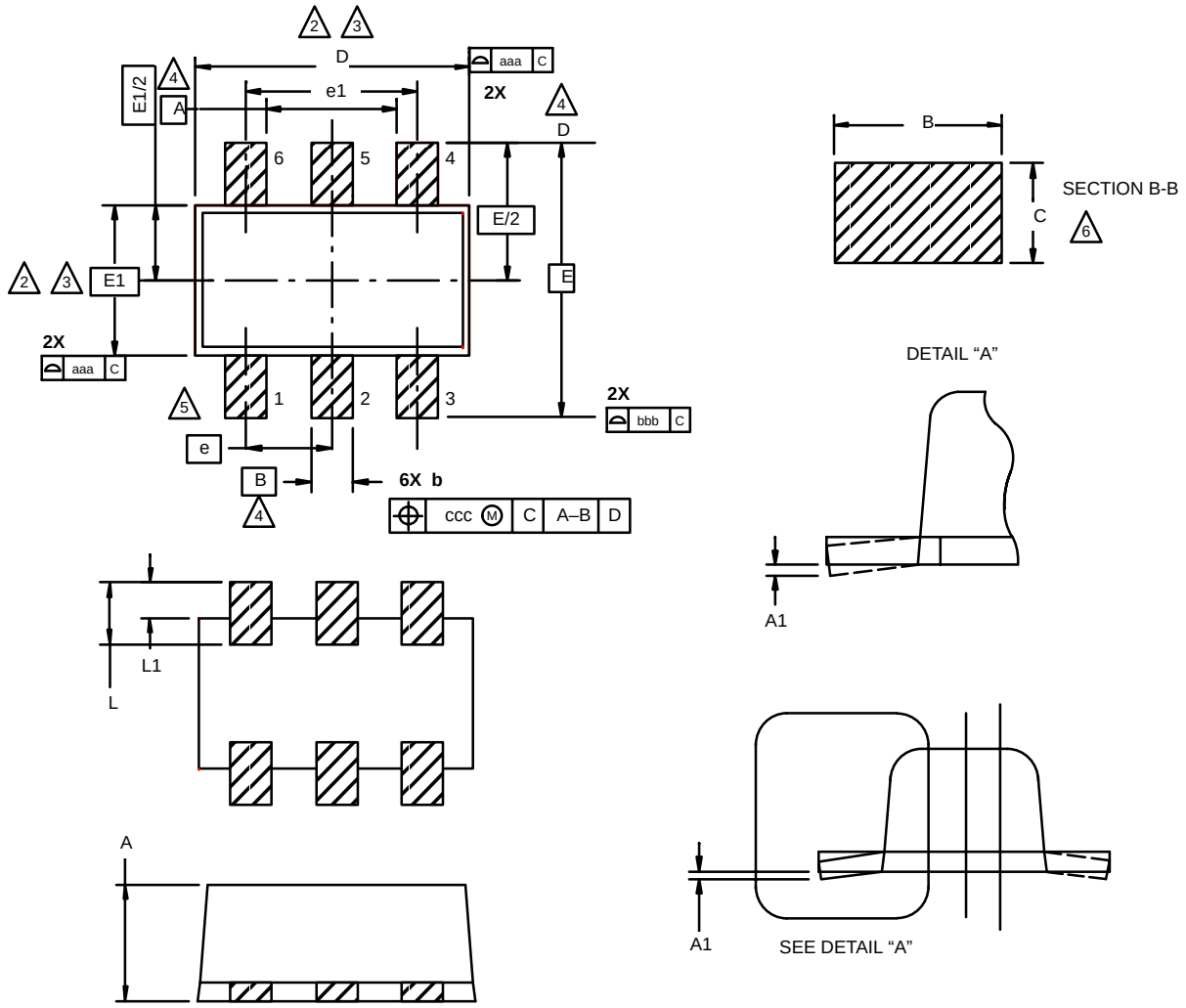
## SC89: 6- LEADS (SOT-563F)




NOTES:

1. Dimensions in millimeters.

2. Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

3. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

4. Datums A, B and D to be determined 0.10 mm from the lead tip.

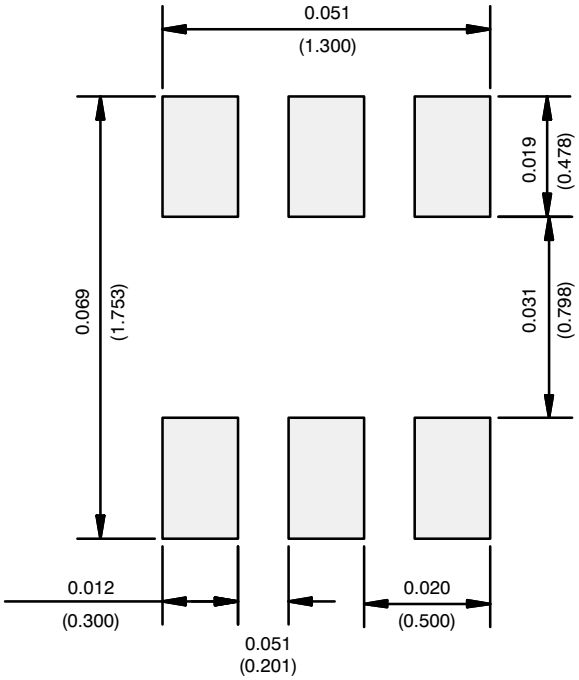
5. Terminal numbers are shown for reference only.

6. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

| Dim | MILLIMETERS | | Note | Symbol | Tolerances Of Form And Position |
|---|---|---|---|---|---|
| | Min | Max | | | |
| **A** | 0.56 | 0.60 | | aaa | 0.10 |
| **A1** | 0.00 | 0.10 | | bbb | 0.10 |
| **b** | 0.15 | 0.30 | | ccc | 0.10 |
| **c** | 0.10 | 0.18 | | | |
| **D** | 1.50 | 1.70 | 2, 3 | | |
| **E** | 1.55 | 1.70 | | | |
| **E1** | 1.20 BSC | | 2, 3 | | |
| **e** | 0.50 BSC | | | | |
| **e1** | 1.00 BSC | | | | |
| **L** | 0.35 BSC | | | | |
| **L1** | 0.20 BSC | | | | |

ECN: E-00499—Rev. B, 02-Jul-01
DWG: 5880

## RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead




Recommended Minimum Pads
Dimensions in Inches/(mm)

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